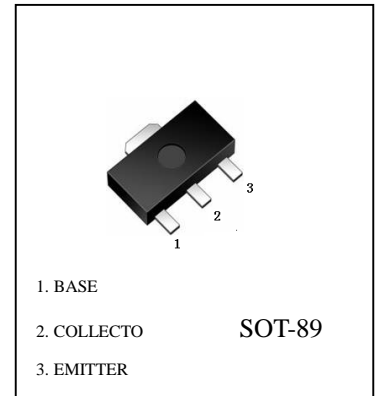


FEATURES

Complimentary to PXT8050

 Collector current: $I_C=1.5A$
MARKING: Y2
MAXIMUM RATINGS ($T_A=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-25	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current -Continuous	I_C	-1500	mA
Collector Power Dissipation	P_C	500	mW
Junction Temperature	T_J	150	$^{\circ}C$
Storage Temperature	T_{stg}	-55-150	$^{\circ}C$

PXT8550 (PNP)

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -0.1mA, I_B = 0$	-25		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu A, I_C = 0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB} = -40V, I_E = 0$		-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -20V, I_B = 0$		-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0$		-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -1V, I_C = -100mA$	85	400	
	$h_{FE(2)}$	$V_{CE} = -1V, I_C = -800mA$	40		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -800mA, I_B = -80mA$		-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -800mA, I_B = -80mA$		-1.2	V
Base-emitter on voltage	$V_{BE(on)}$	$I_C = -1V, V_{CE} = -10mA$		-1	V
Base-emitter positive forward voltage	V_{BEF}	$I_B = -1A$		-1.55	V
Transition frequency	f_T	$V_{CE} = -10V, I_C = -50mA$	100		MHz
output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$		20	pF

CLASSIFICATION OF HFE

Rank	B	C	D	D3
Range	85-160	120-200	160-300	300-400

PXT8550 Typical Characteristics

